

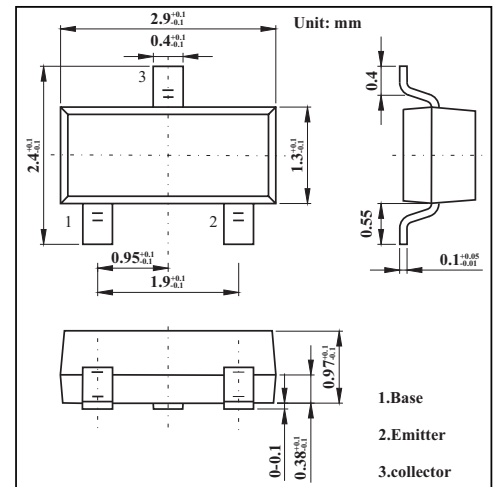
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low collector to emitter saturation voltage
- General purpose amplifier applications
- PNP Transistor

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CB0}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	500	mA
Peak collector current	I_{CP}	1	A
Collector power Dissipation	P_C	200	mW
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=150mA$	85		340	
		$V_{CE}=10V, I_C=500mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=300mA, I_B=30mA$		0.35	0.6	V
Transition frequency	f_T	$V_{CB}=10V, I_E=-50mA, f=200MHz$		200		MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		6	15	pF

RATINGS AND CHARACTERISTIC CURVES

